

Amendments to the Specification:

Please replace the abstract at page 11 with the following amended abstract:

--~~Radiation-emitting semiconductor component~~

In a radiation-emitting semiconductor component with a layer structure comprising an n-doped confinement layer [[(14)]], a p-doped confinement layer [[(22)]], and an active, photon-emitting layer [[(18)]] disposed between the n-doped confinement layer [[(14)]] and the p-doped confinement layer [[(22)]], it is provided according to the invention that the n-doped confinement layer [[(14)]] is doped with a first n-dopant (or two mutually different n-dopants) for producing high active doping and a sharp doping profile, and the active layer [[(18)]] is doped with only one second n-dopant, different from the first dopant, for improving the layer quality of the active layer [[(18)]].

Figure 1--